NEC

THYRISTORS

AC03DGM, AC03FGM

3 A MOLD TRIAC

The AC03EGM and AC03FGM are fully diffused mold TRIACs with an effective on-current of 3 A. The repeat peak off-voltages are 400 V and 600 V.

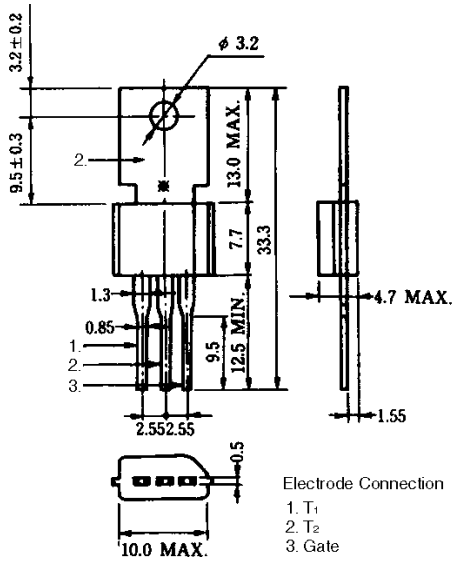
FEATURES

- Gate trigger current (mode I, III, and IV) at 12 mA or less is guaranteed.
- This transistor features a small and lightweight package and is easy to handle even on the mounting surface due to its TO-202AA dimensions. Processing of lead wires and heatsink (tablet) using jigs is also possible.
- High degrees-of-freedom applications design is available due to high gate trigger sensitivity and small hold current distribution.
- Employs flame-retardant epoxy resin (UL94V-0).

APPLICATIONS

Noncontact switches of motor speed control, heater temperature control, lamp light control

PACKAGE DRAWING (UNIT: mm)



*T_C test bench-mark Standard weight: 1.4 g

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	AC03DGM	AC03FGM	Unit	Remarks
Non-repetitive peak off-state voltage	V_{DSM}	500	700	V	–
Repetitive peak off-voltage	V_{DRM}	400	600	V	–
Effective on-state current	$I_{T(RMS)}$	3 (T_C = 92°C)		A	Refer to Figures 11 and 12.
Surge on-state current	I_{TSM}	30 (50 Hz 1 cycle) 33 (60 Hz 1 cycle)		A	Refer to Figure 2.
Fusing current	$\int i_T^2 dt$	4.0 (1 ms ≤ t ≤ 10 ms)		A^2s	–
Critical rate of rise of on-state current	dI_T/dt	40		A/μs	–
Peak gate power dissipation	P_{GM}	3 (f ≥ 50 Hz, Duty ≤ 10 %)		W	–
Average gate power dissipation	$P_{G(AV)}$	0.3		W	–
Peak gate current	I_{GM}	±0.5 (f ≥ 50 Hz, Duty ≤ 10 %)		A	–
Junction temperature	T_j	–40 to +125		°C	–
Storage temperature	T_{stg}	–55 to +150		°C	–

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Document No. D13536EJ3V0DS00 (3rd edition)
Date Published April 2002 N CP(K)
Printed in Japan

ELECTRICAL CHARACTERISTICS (Tj = 25°C, RGK = 1 kΩ)

Parameter		Symbol	Conditions		MIN.	TYP.	MAX.	Unit	Remarks
Repeat peak off-current		I_{DRM}	$V_{DM} = V_{DRM}$	T_j = 25°C	–	–	100	μA	–
				T_j = 125°C	–	–	1	mA	
On-state voltage		V_{TM}	I_{TM} = 5 A		–	–	1.8	V	Refer to Figure 1.
Gate trigger current	Mode I	I_{GT}	V_{DM} = 12 V, R_L = 30 Ω	T_2 +, G+	–	–	12	mA	Refer to Figure 4.
	II			T_2 –, G+	–	–	–		
	III			T_2 –, G–	–	–	12		
	IV			T_2 +, G–	–	–	12		
Gate trigger voltage	Mode I	V_{GT}	V_{DM} = 12 V, R_L = 30 Ω	T_2 +, G+	–	–	1.5	V	Refer to Figure 4.
	II			T_2 –, G+	–	–	–		
	III			T_2 –, G–	–	–	1.5		
	IV			T_2 +, G–	–	–	1.5		
Gate non-trigger voltage		V_{GD}	T_j = 125°C, $V_{DM} = \frac{1}{2} V_{DRM}$		0.2	–	–	V	–
Hold current		I_H	V_{DM} = 24 V, I_{TM} = 5 A		–	10	–	mA	–
Critical rate of rise of off-state voltage		dv/dt	T_j = 125°C, $V_{DM} = \frac{2}{3} V_{DRM}$		–	100	–	V/μs	–
Commutating critical rate of rise of off-state voltage		(dv/dt)c	T_j = 125°C, $(di_T/dt)c$ = –1.6 A/ms, V_D = 400 V		5	–	–	V/μs	–
Thermal resistance*		$R_{th(j-c)}$	Junction-to-case AC		–	–	10	°C/W	Refer to Figure 13.
		$R_{th(j-a)}$	Junction-to-ambient AC		–	–	75	°C/W	

* The thermal resistance at 50 Hz and 60 Hz sine wave current, which is shown on the following expression:

$$R_{th(j-c)} = \frac{T_{j(max)} - T_C}{P_{T(AV)}}$$

$T_{j(max)}$:Maximum junction temperature

T_C :Case temperature

$P_{T(AV)}$:Average on-dissipation

Figure 1. i_T vs. v_T Characteristics

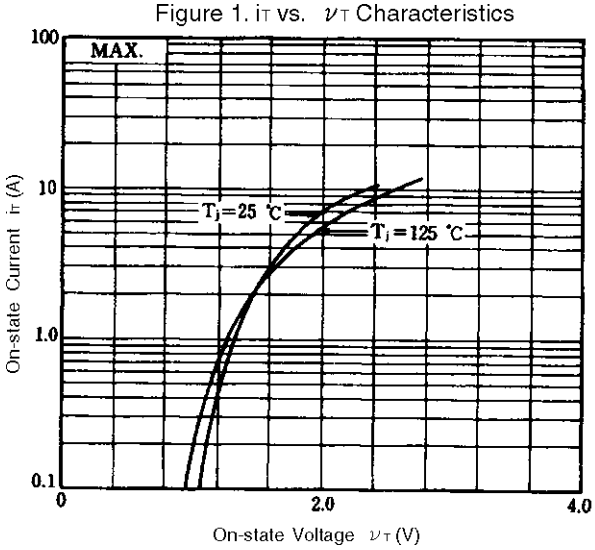


Figure 2. I_{TSM} Rating

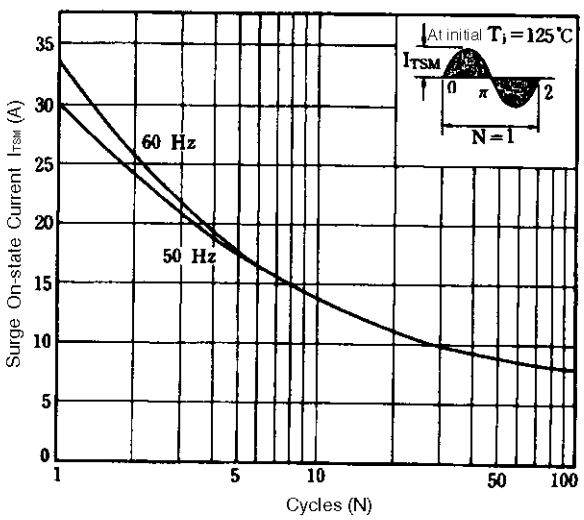


Figure 3. Gate Rating

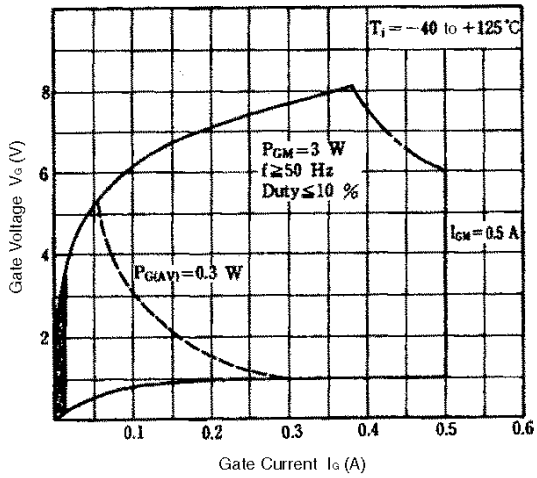


Figure 4. Example of Gate Characteristics

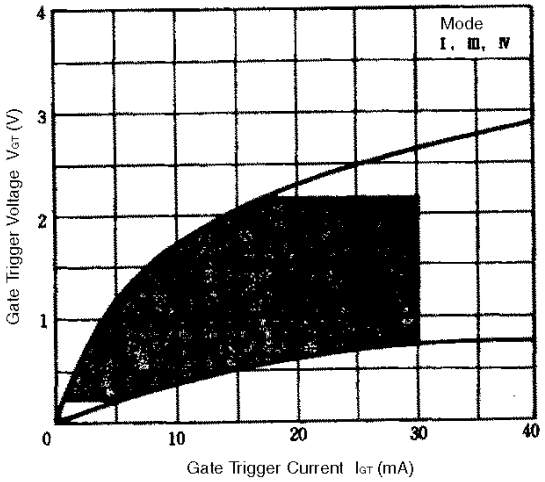


Figure 5. I_{GT} vs. T_A Example of Characteristics

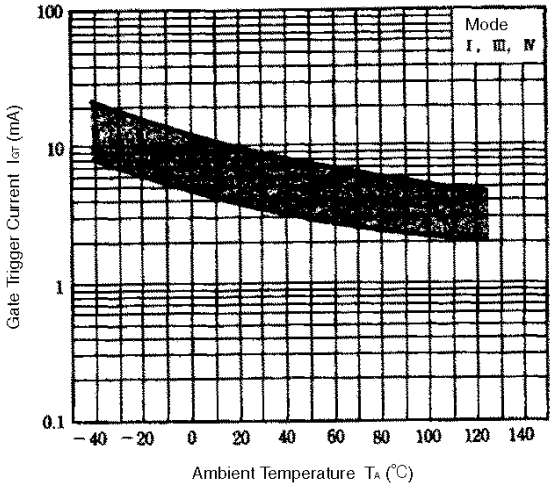


Figure 6. V_{GT} vs. T_A Example of Characteristics

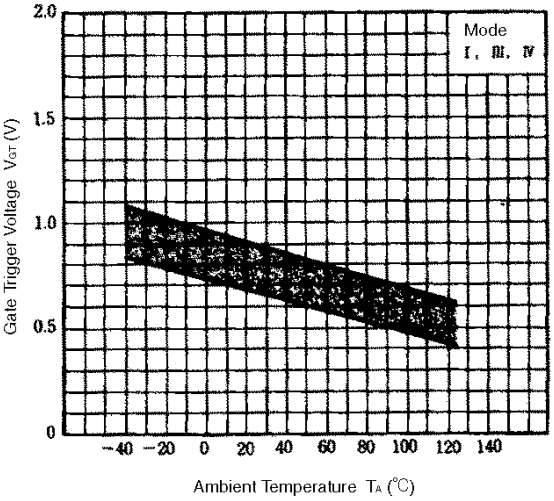


Figure 7. i_{GT} vs. τ Example of Characteristics

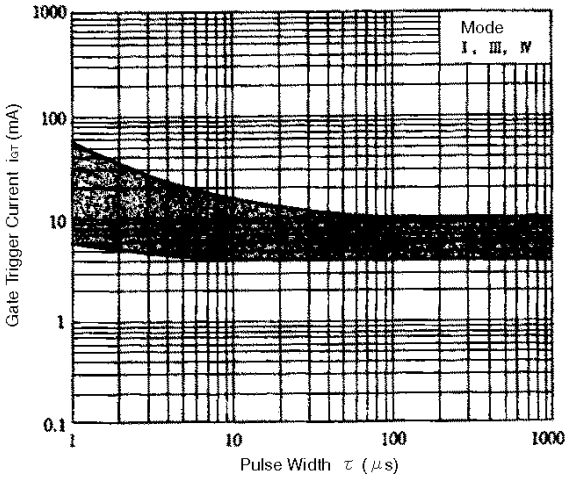


Figure 8. υ_{GT} vs. τ Example of Characteristics

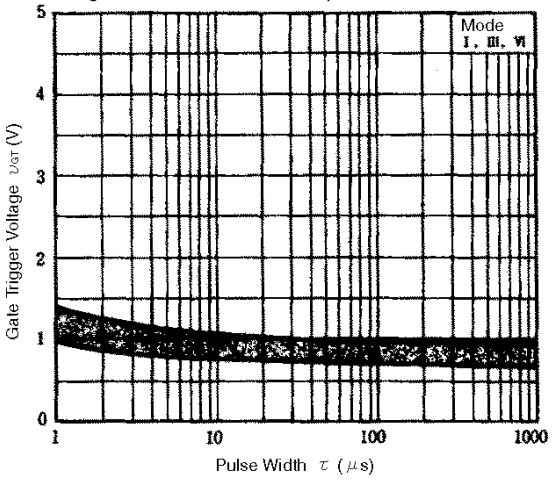


Figure 9. I_H vs. T_A Example of Characteristics

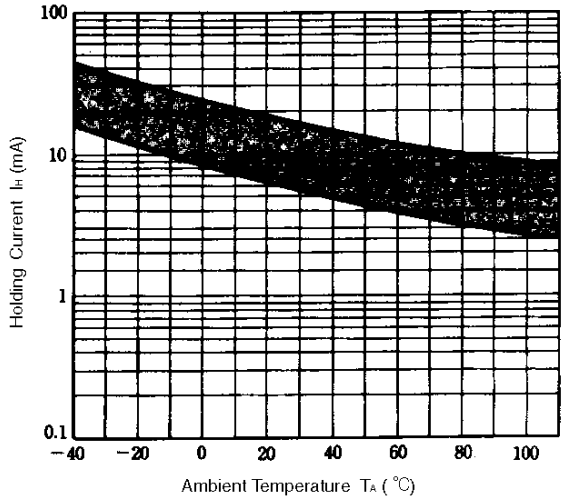


Figure 10. $P_{T(AV)}$ vs. $I_{T(RMS)}$ Characteristics

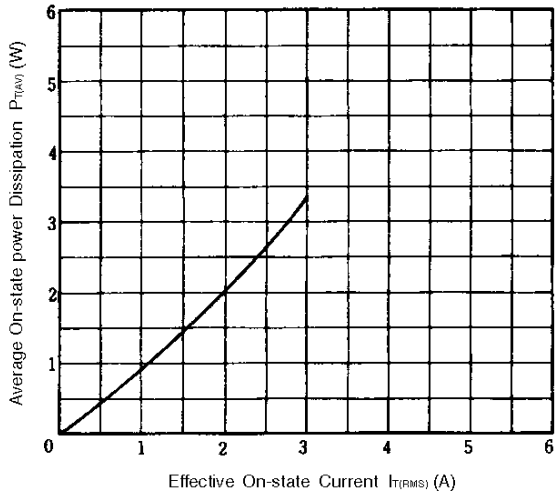


Figure 11. T_C vs. $I_{T(AV)}$ Rating

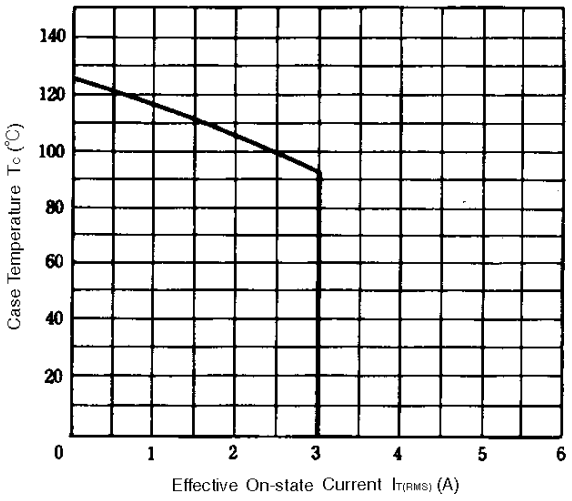


Figure 12. T_A vs. $I_{T(RMS)}$ Rating

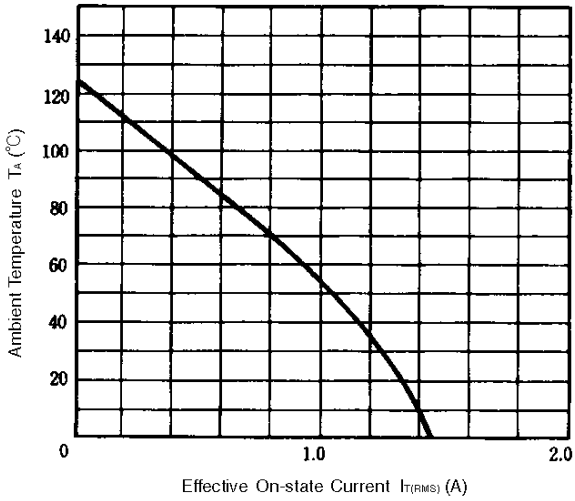
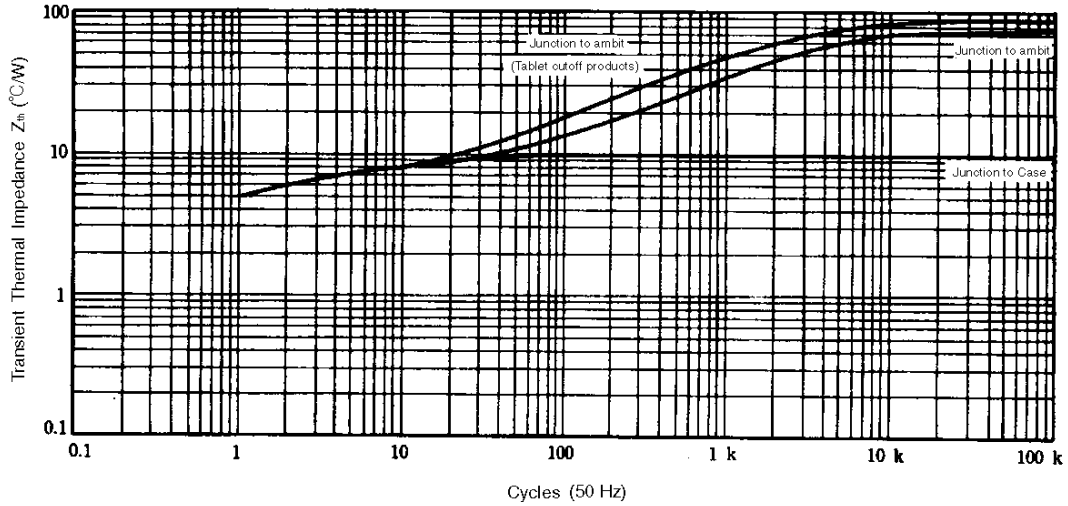


Figure 13. Z_{th} Characteristics



[MEMO]

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